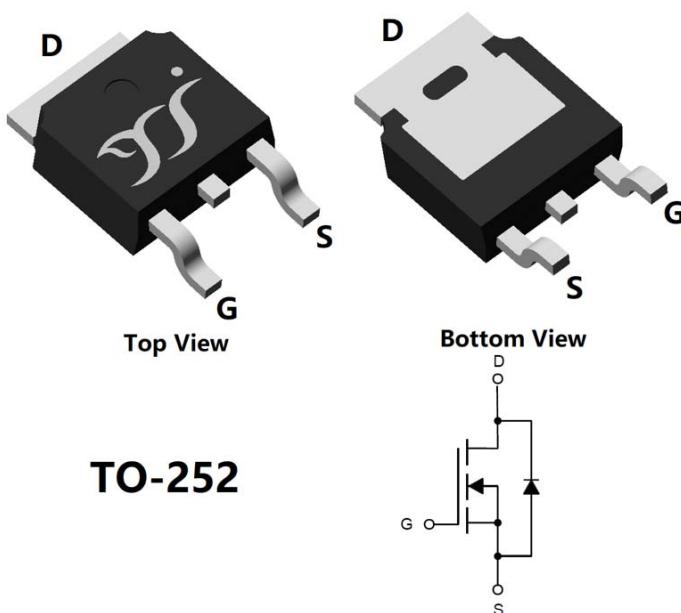


N-Channel Enhancement Mode Field Effect Transistor

**TO-252**

Product Summary

- V_{DS} 40V
- I_D 140A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) $<2.8m\Omega$
- 100% EAS Tested
- 100% ∇V_{DS} Tested

General Description

- Low $R_{DS(on)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity
- Fast switching and soft recovery
- Moisture Sensitivity Level 1
- Part no. with suffix "Q" means AEC-Q101 qualified

Applications

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply
- DC-DC convertor
- 12V Automotive systems

■ Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	V_{DS}	40	V
Gate-source Voltage	V_{GS}	± 20	V
Drain Current	I_D	140	A
		99	
		25	
		17	
Pulsed Drain Current ^A	I_{DM}	400	A
Avalanche energy ^B	EAS	315	mJ
Total Power Dissipation ^C	P_D	100	W
		50	
		3	
		1.5	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 ~ +175	°C

**■ Thermal resistance**

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient ^D	Steady-State	R _{θJA}	40	50	°C/W
Thermal Resistance Junction-to-Case	Steady-State	R _{θJC}	1.2	1.5	

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJD2D8G04HHQ	F1	YJD2D8G04H	2500	/	25000	13"Reel

- A. Repetitive rating; pulse width limited by max. junction temperature.
- B. T_j=25°C, V_{DD}=30V, V_G=10V, R_G=25Ω, L=0.5mH, IAS=35.5A.
- C. P_d is based on max. junction temperature, using junction-case thermal resistance.
- D. The value of R_{θJA} is measured with the device mounted on the minimum recommend pad size, in the still air environment with T_A=25°C. The maximum allowed junction temperature of 175°C. The value in any given application depends on the user's specific board design.

■ Electrical Characteristics ($T_J=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	40			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=40V, V_{GS}=0V$			1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2	3	4	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=20A$		2.2	2.8	$m\Omega$
Diode Forward Voltage	V_{SD}	$I_S=20A, V_{GS}=0V$		0.8	1.2	V
Gate resistance	R_G	f=1MHz		2		Ω
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V, f=1MHz$	-	3344	-	pF
Output Capacitance	C_{oss}		-	977	-	
Reverse Transfer Capacitance	C_{rss}		-	39	-	
Switching Parameters						
Total Gate Charge	Q_g	$V_{GS}=10V, V_{DS}=20V, I_D=45A$	-	42.2	-	nC
Gate-Source Charge	Q_{gs}		-	15.4	-	
Gate-Drain Charge	Q_{gd}		-	9.4	-	
Reverse Recovery Charge	Q_{rr}	$I_F=30A, di/dt=150A/us$	-	40	-	nC
Reverse Recovery Time	t_{rr}		-	38	-	ns
Turn-on Delay Time	$t_{D(on)}$	$V_{GS}=10V, V_{DD}=20V, I_D=45A$ $R_{GEN}=2.2\Omega$	-	20.3	-	ns
Turn-on Rise Time	t_r		-	209	-	
Turn-off Delay Time	$t_{D(off)}$		-	25	-	
Turn-off fall Time	t_f		-	12.3	-	

■Typical Electrical and Thermal Characteristics Diagrams

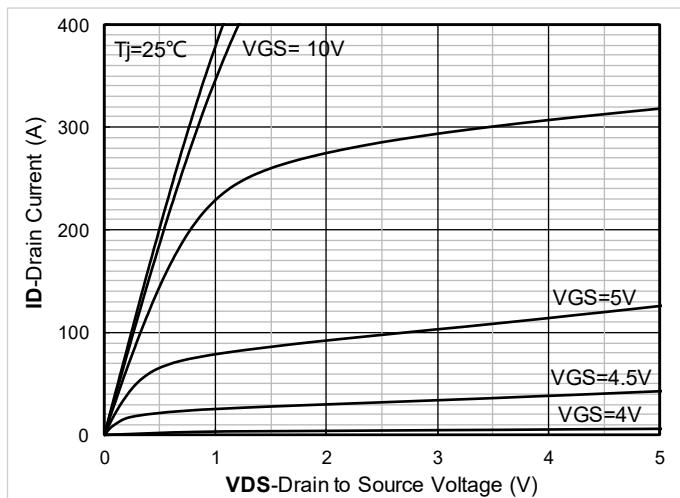


Figure 1. Output Characteristics

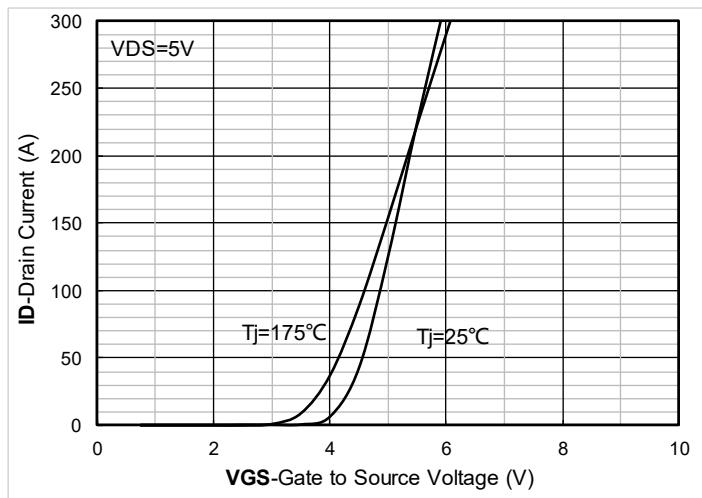


Figure 2. Transfer Characteristics

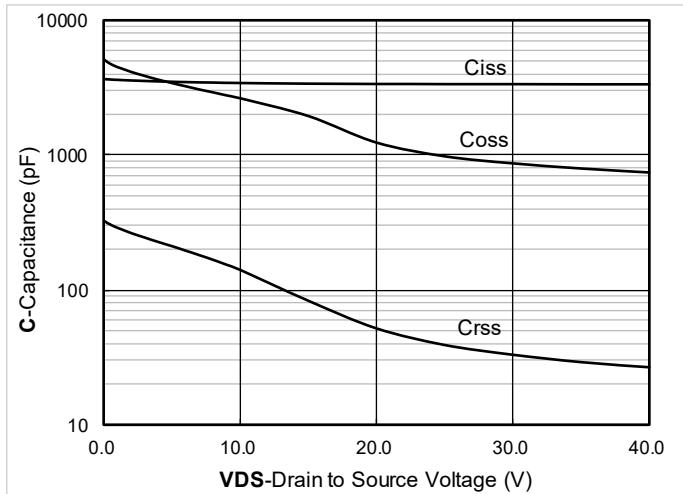


Figure 3. Capacitance Characteristics

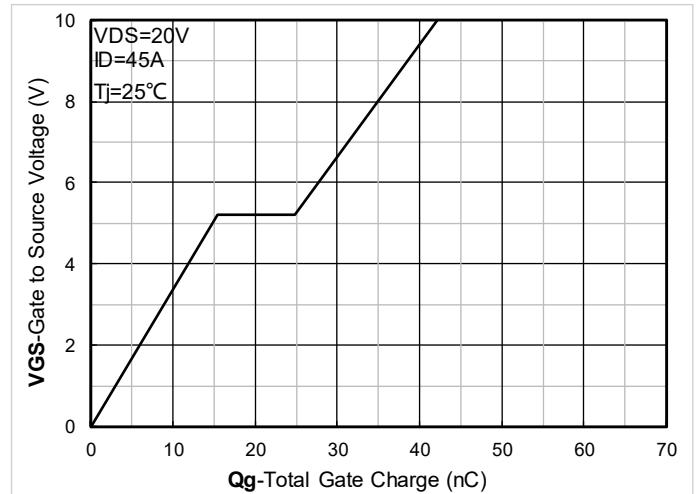


Figure 4. Gate Charge

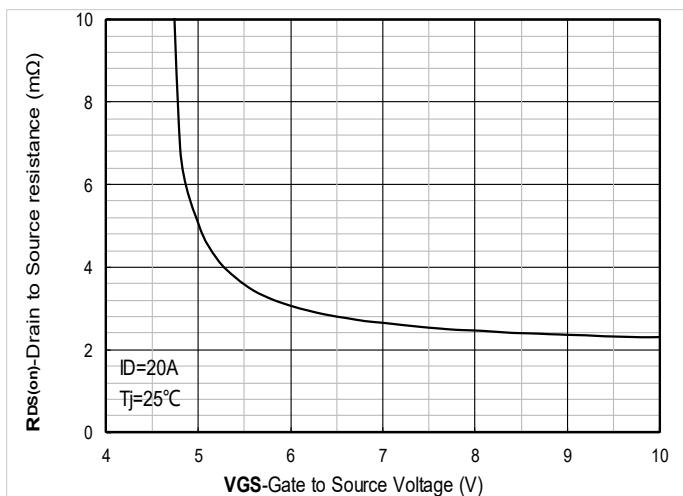


Figure 5. On-Resistance vs Gate to Source Voltage

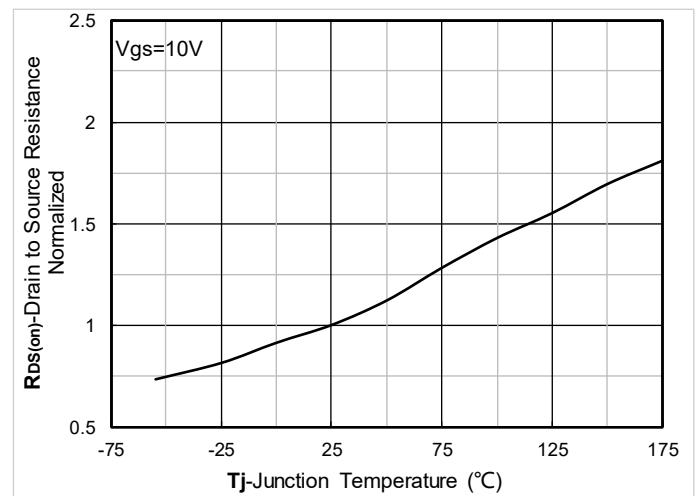


Figure 6. Normalized On-Resistance

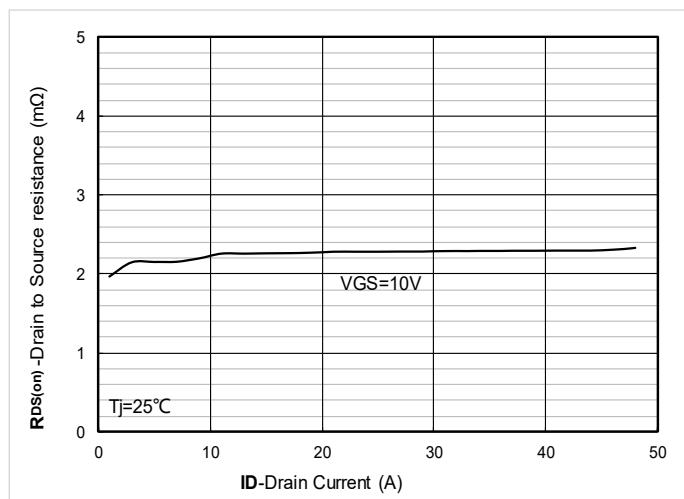


Figure 7. RDS(on) VS Drain Current

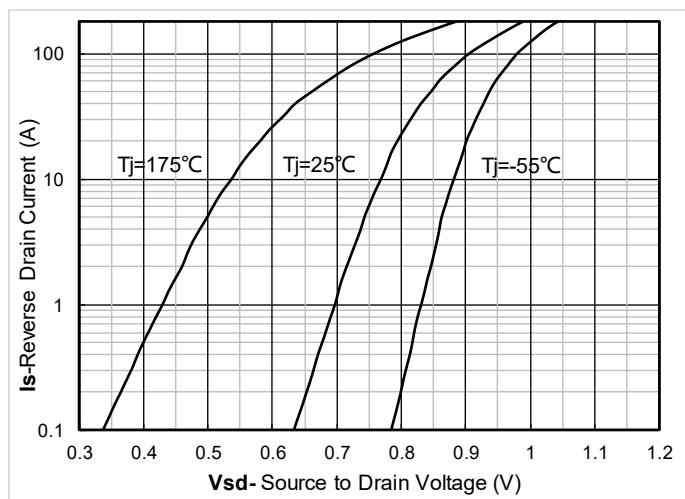


Figure 8. Forward characteristics of reverse diode

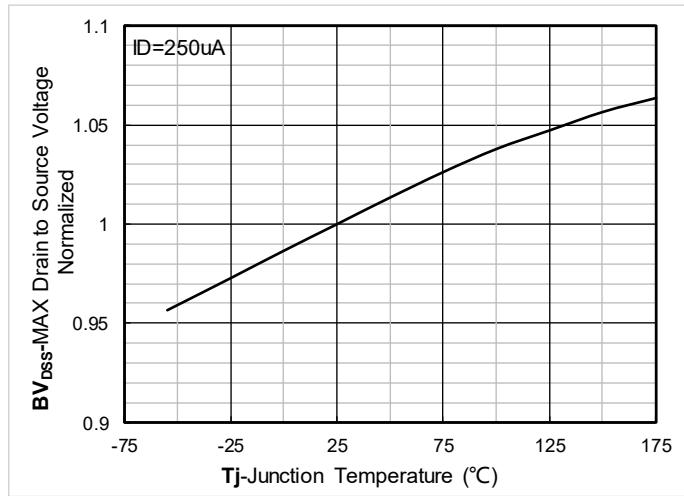


Figure 9. Normalized breakdown voltage

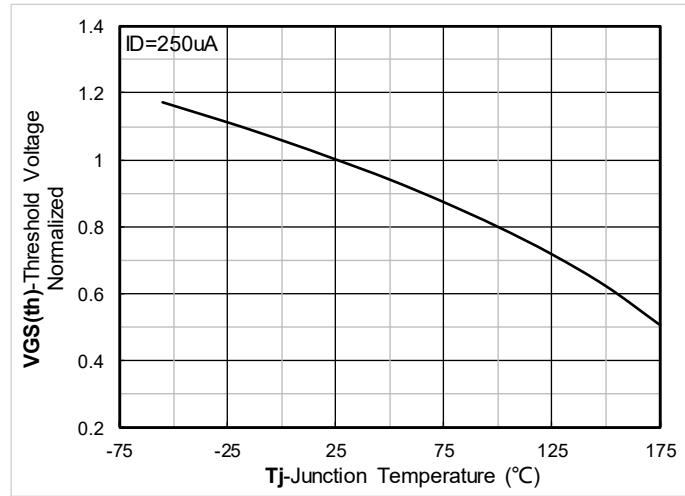


Figure 10. Normalized Threshold voltage

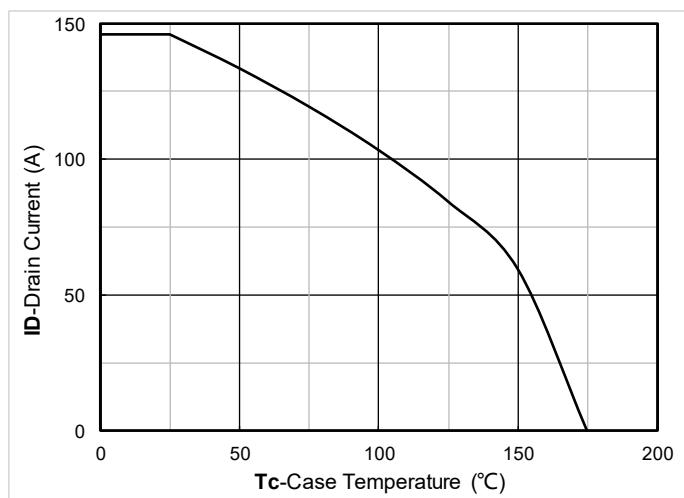


Figure 11. Current dissipation

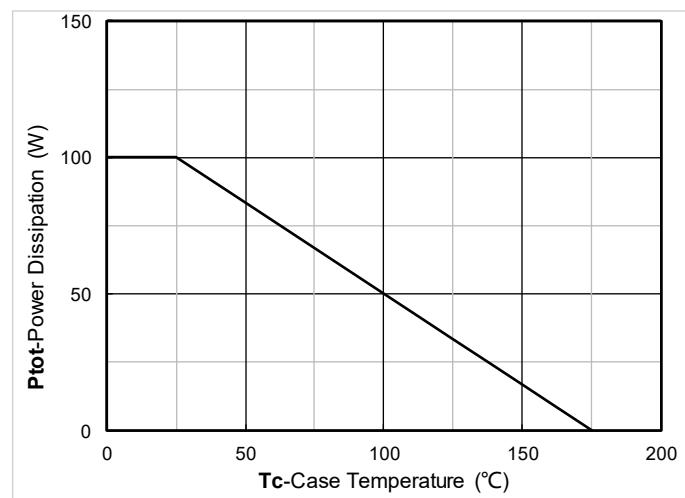


Figure 12. Power dissipation

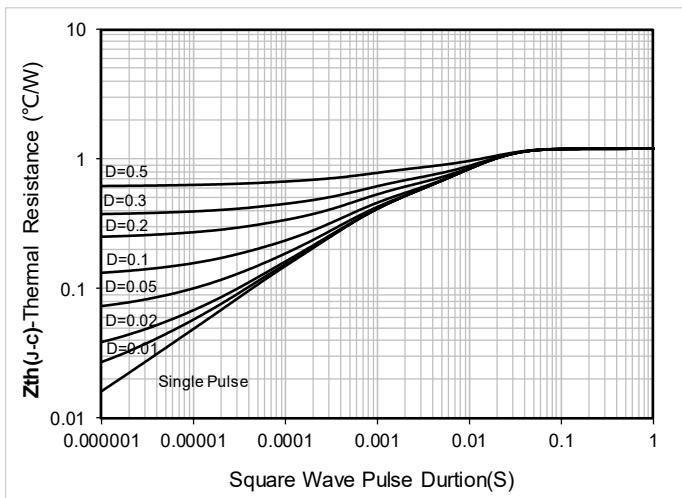


Figure 13. Maximum Transient Thermal Impedance

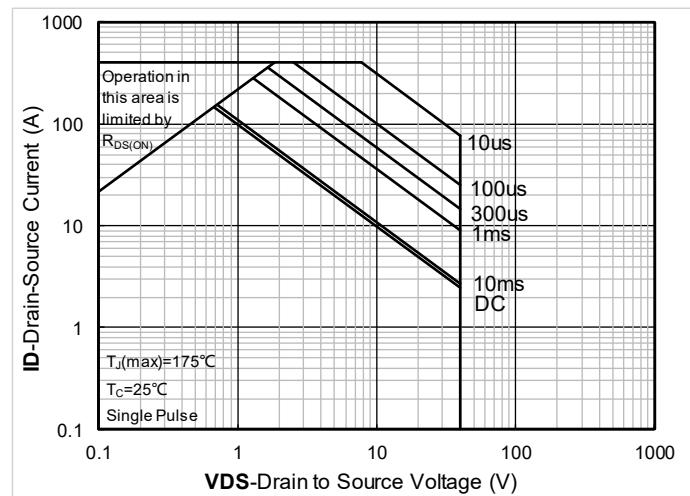
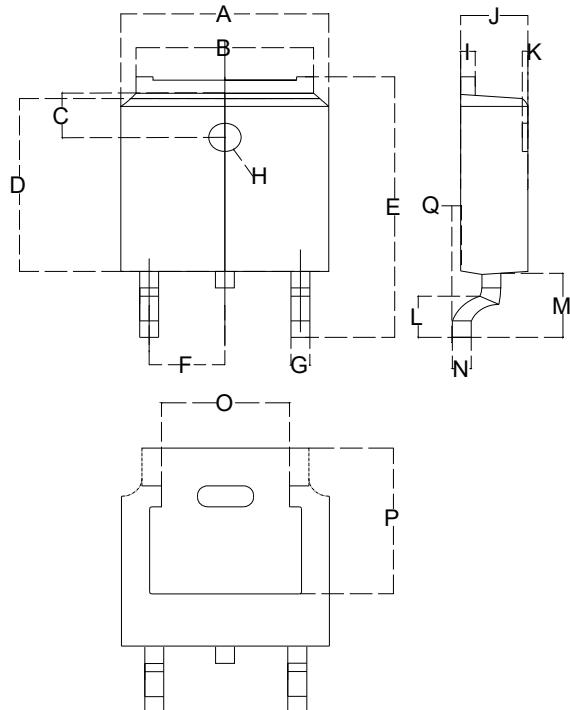


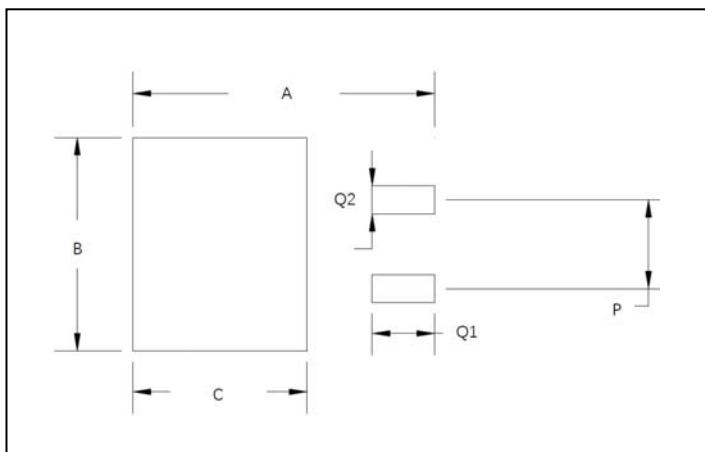
Figure 14. Safe Operation Area

■ TO-252 Package information

TO-252

**Dimensions in millimeters**

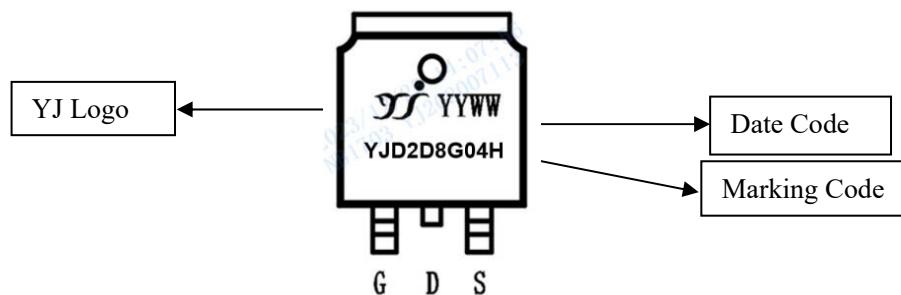
TO-252		
Dim	Min	Max
A	6.500	6.700
B	5.100	5.460
C	1.400	1.800
D	6.000	6.200
E	10.000	10.400
F	2.166	2.366
G	0.660	0.860
H	Φ 1.050	Φ 1.350
I	0.460	0.580
J	2.200	2.400
K	0	0.300
L	0.890	2.290
M	2.730	3.080
N	0.430	0.580
O	3.800	4.500
P	5.15	5.45
Q	0	0.2

■ Suggested Pad Layout

Dim	Millimeters
A	11.4
B	6.74
C	6.23
P	4.56
Q1	2.28
Q2	1.52



■ Marking Information



Note:

1. All marking is at middle of the product body
2. All marking is in laser printing
3. YJD2D8G04H is Marking Code, YYWW is date code, "YY" is year, "WW" is week
4. Body color: Black



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